

# **Description**

The HXY5N10MI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

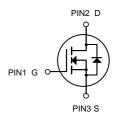


#### **General Features**

 $V_{DS} = 100V I_{D} = 5A$ 

 $R_{DS(ON)}$  < 120m $\Omega$  @  $V_{GS}$ =10V

 $R_{DS(ON)}$  < 143m $\Omega$  @  $V_{GS}$ =4.5V



#### N-Channel MOSFET

# **Application**

Battery protection

Load switch

Uninterruptible power supply

# **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
HXY5N10MI	SOT-23-3L	1005	3000

# Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	100	V
VGS	Gate-Source Voltage	±20	V
lo	Drain Current-Continuous	5	А
IDM	Drain Current-Pulsed (Note 1)	20	Α
P <sub>D</sub>	Maximum Power Dissipation	1.5	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 175	°C
RθJA	Thermal Resistance,Junction-to-Ambient (Note 2)	100	°C/W



# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	100	-	-	V
Zero Gate Voltage Drain Current	Ipss	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	Igss	$V_{GS}$ =±20 $V$ , $V_{DS}$ =0 $V$	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	1.0	1.5	2.0	V
		V <sub>GS</sub> =10V, I <sub>D</sub> =3A	-	100	120	mΩ
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	130	143	
Forward Transconductance	grs	V <sub>DS</sub> =5V,I <sub>D</sub> =3A	-	5	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	Clss	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V,	-	650	-	PF
Output Capacitance	Coss		-	24	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	20	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	td(on)		-	6	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =50V, $R_L$ =19 $\Omega$	-	4	-	nS
Turn-Off Delay Time	td(off)	$V_{GS}$ =10 $V_{,R_G}$ =3 $\Omega$	-	20	-	nS
Turn-Off Fall Time	tf		-	4	-	nS
Total Gate Charge	Qg		-	20		nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =50V,I <sub>D</sub> =3A,	-	2.1	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	3.3	-	nC
Drain-Source Diode Characteristics	- 1		1			
Diode Forward Voltage (Note 3)	VsD	V <sub>GS</sub> =0V,I <sub>S</sub> =3A	-	-	1.2	V
Diode Forward Current (Note 2)	ls		-	-	3	Α

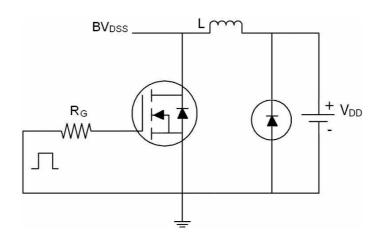
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

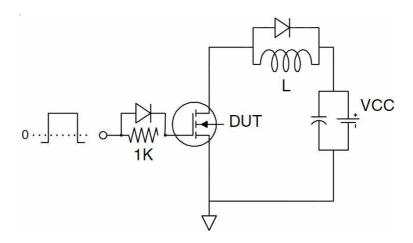


### **Test Circuit**

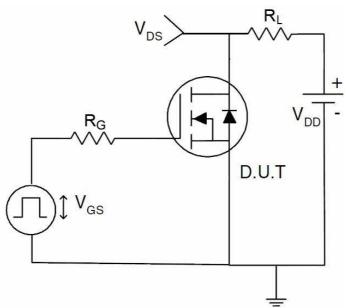
## 1) E<sub>AS</sub> test circuit



## 2) Gate charge test circuit

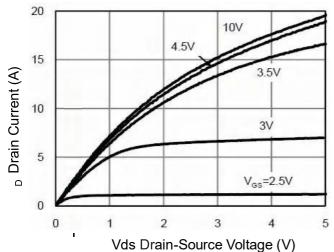


## 3) Switch Time Test Circuit





# Typical Electrical and Thermal Characteristics (Curves)



**Figure 1 Output Characteristics** 

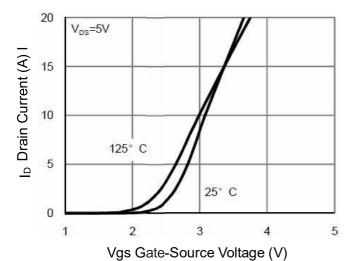
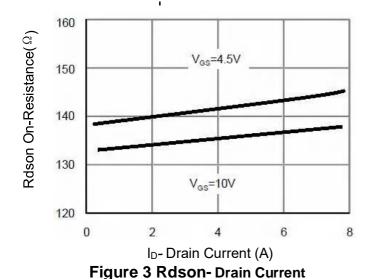


Figure 2 Transfer Characteristics



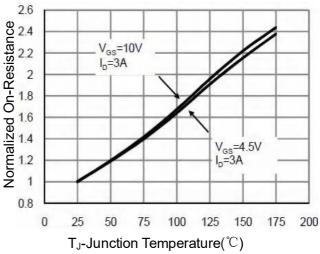


Figure 4 Rdson-JunctionTemperature

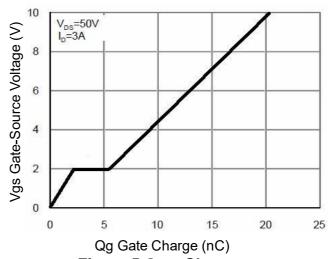


Figure 5 Gate Charge

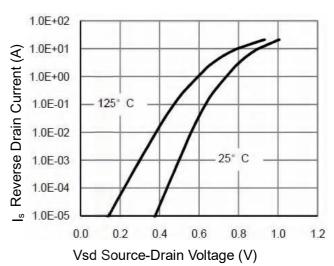


Figure 6 Source- Drain Diode Forward

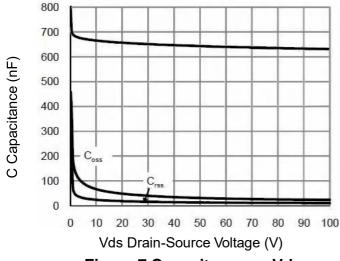


Figure 7 Capacitance vs Vds

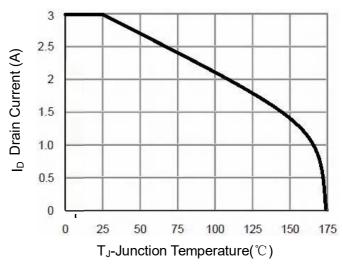
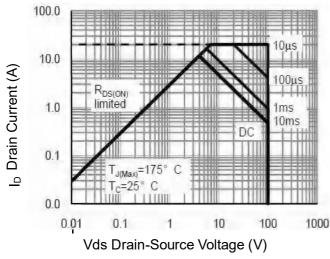


Figure 9 BV<sub>DSS</sub> vs Junction Temperature



**Figure 8 Safe Operation Area** 

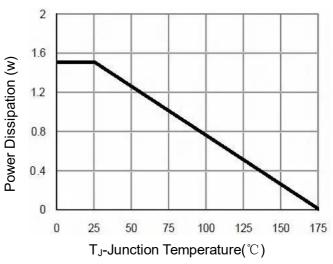
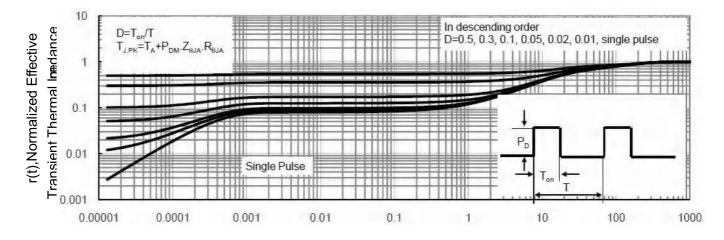


Figure 10 Power De-rating

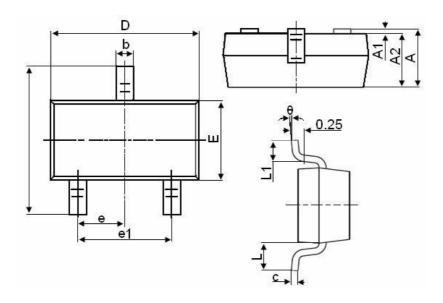


Square Wave Pluse Duration(sec)

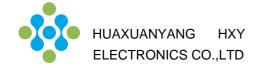
**Figure 11 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23-3L Package Information**



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е		0.950TYP	
e1	1.800	2.000	
L		0.550REF	
L1	0.300	0.600	
θ	0°	8°	



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